

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND
PROGRAM

ABSTRACT

There is provided a technique that includes (a) forming a layer including a surface terminated with an element X on a surface of a substrate by supplying an element X-containing gas to the substrate which is set to have a first temperature, (b) changing a surface termination with the element X on the surface of the layer to a surface termination with an element Y by supplying an element Y-containing gas to the substrate which is set to have a second temperature, (c) desorbing the element Y constituting the surface termination with the element Y on the surface of the layer by setting the substrate to have a third temperature, and (d) forming a film on the layer from which the element Y is desorbed, by supplying a film-forming gas to the substrate which is set to have a fourth temperature.

Fig.4